MT60C-T1

RoHS COMPLIANT

Thyristor Modules

V_{RRM} / V_{DRM} 800 to 1800V
I_{TAV} 60A

Features

- International standard package
- High Surge Capability
- Glass passivated chip
- Simple Mounting
- Heat transfer through aluminum oxide DBC ceramic isolated metal baseplate
- UL recognized applied for file no. E360040

Module Type

TYPE	V_{RRM}	V_{RSM}
MT60C08T1	800V	900V
MT60C12T1	1200V	1300V
MT60C16T1	1600V	1700V
MT60C18T1	1800V	1900V

Maximum Ratings

Symbol	Conditions	Values	Units
I_{TAV}	Sine 180°;Tc=85	60	A
I_{TSM}	T_{VJ}=45 t=10ms, sine T_{VJ}=125 t=10ms, sine	1500 1250	A
i^2t	T_{VJ}=45 t=10ms, sine T_{VJ}=125 t=10ms, sine	11000 8000	A^2s
Visol	a.c.50HZ;r.m.s.;1min	3000	V
Tvj		-40 to 125	

Thermal Characteristics

Electrical Characteristics

Symbol	Conditions	Values			Units
		Min.	Typ.	Max.	
V_{TM}	T=25 I_{TM} =200A			1.65	V
I_{RRM}/I_{DRM}	T_{VJ} =T_{VJM} ,V_R=V_{RRM} ,V_D=V_{DRM}			15	mA
V_{TO}	For power-loss calculations only (T_{VJ} =125)			0.9	V
r_T	T_{VJ} =T_{VJM}			3.5	mΩ
V_{GT}	T_{VJ} =25 , V_D =6V			3.0	V
I_{GT}	T_{VJ} =25 , V_D =6V			150	mA
V_{GD}	T_{VJ} =125 , V_D =2/3V_{DRM}			0.25	V
I_{GD}	T_{VJ} =125 , V_D =2/3V_{DRM}			6	mA
I_L	T_{VJ} =25 , R_G = 33 Ω		300	600	mA
I_H	T_{VJ} =25 , V_D =6V		150	250	mA
tgd	T_{VJ} =25 , I_G=1A, di_G/dt=1A/us		1		us
tq	T_{VJ} =T_{VJM}		80		us

Performance Curves